

**Appln No. 09/423,401**  
**Amdt date May 1, 2006**  
**Reply to Office action of January 30, 2006**

**Amendments to the Specification:**

Please replace paragraph on page 12, lines 22-25 with the following amended paragraph:

The dielectric layer may be made of any reactive dielectric material which contains basic elements of silicon ~~silicon~~ and oxygen, such as SiO<sub>2</sub> or silica, and may be deposited by any deposition method. This layer may also contain other elements such as N and F.